



GP
ELECTRONICS

GP3134K-T

20V N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
20V	190mΩ@4.5V	0.75A
	260mΩ@2.5V	
	390mΩ@1.8V	

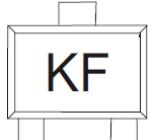
Feature

- Lead Free Product is Acquired
- Surface Mount Package
- N-Channel Switch with Low $R_{DS(on)}$
- Operated at Low Logic Level Gate Drive

Application

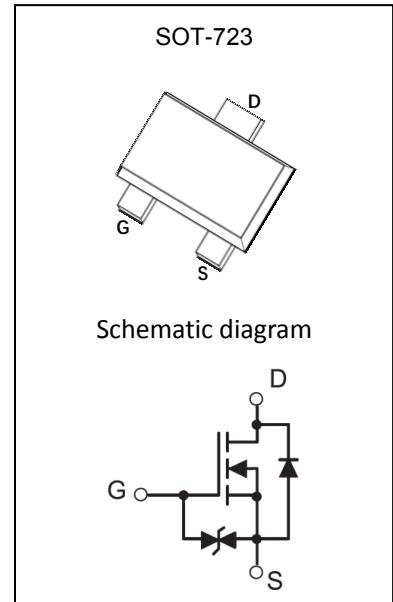
- Load/Power Switching
- Interfacing Switching
- Battery Management for Ultra Small Portable Electronics
- Logic Level Shift

MARKING:



ABSOLUTE MAXIMUM RATINGS ($T_a=25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Gate-Source Voltage	V_{GS}	± 12	V
Continuous Drain Current ⁽¹⁾	I_D	0.75	A
Pulsed Drain Current($t_p=10\mu\text{s}$)	I_{DM}	1.8	A
Power Dissipation ⁽¹⁾	P_D	150	mW
Thermal Resistance from Junction to Ambient ⁽¹⁾	$R_{\theta JA}$	833	°C/W
Junction Temperature	T_J	150	°C
Storage Temperature	T_{STG}	-55~+150	°C
Lead Temperature for Soldering Purposes(1/8" from case for 10s)	T_L	260	°C



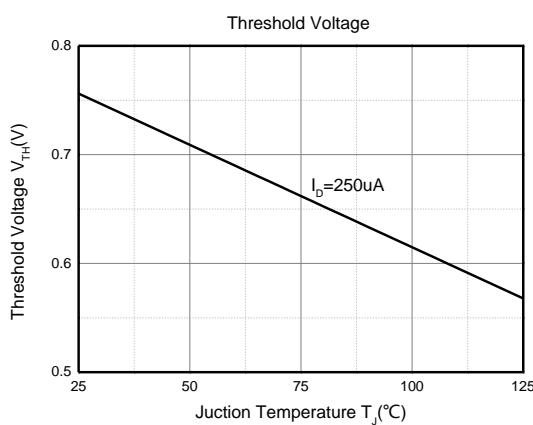
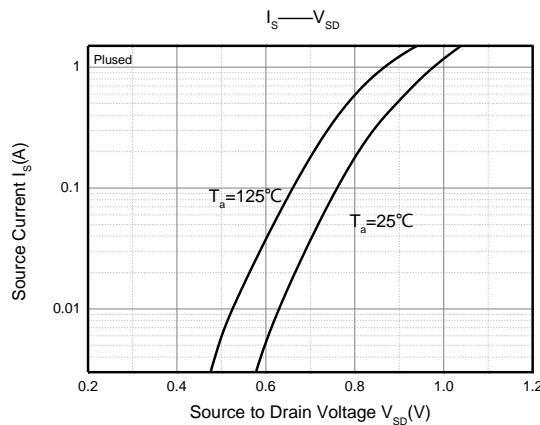
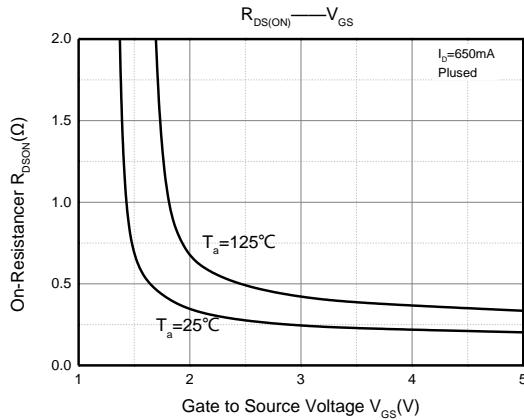
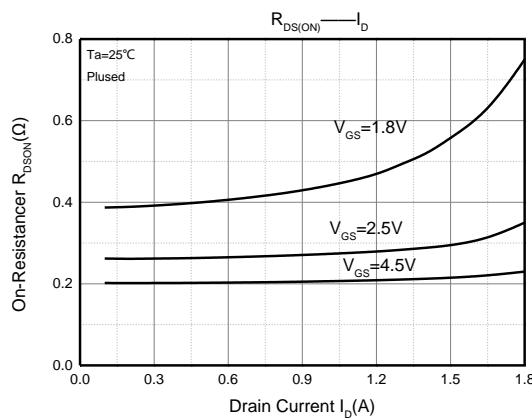
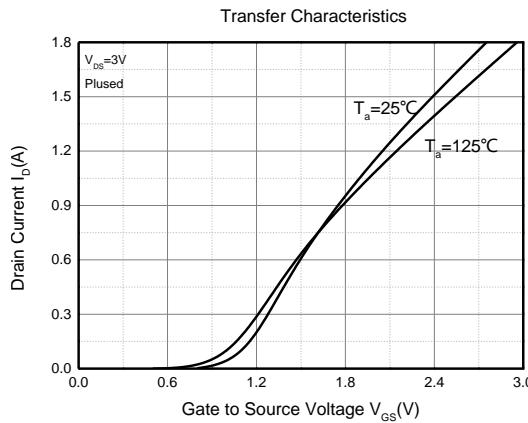
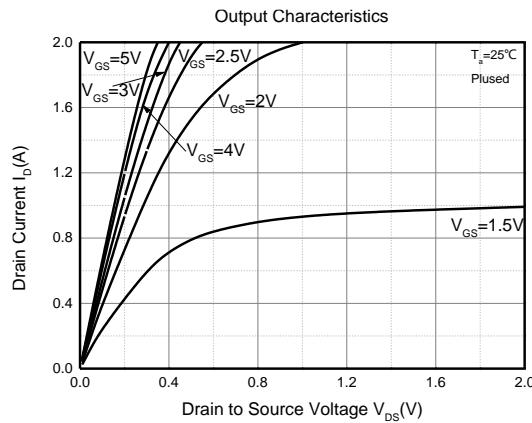
MOSFET ELECTRICAL CHARACTERISTICS($T_a=25^\circ\text{C}$ unless otherwise noted)

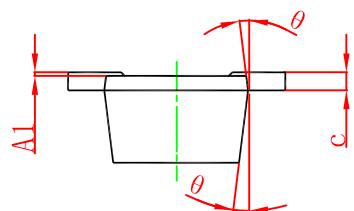
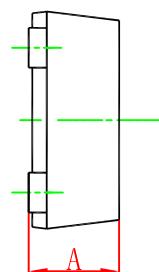
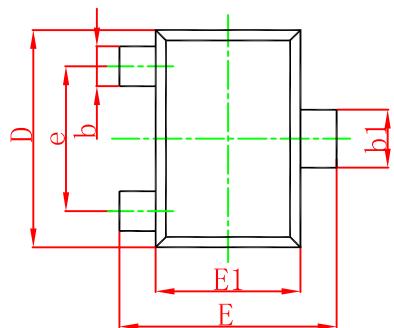
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Static Characteristics						
Drain-source breakdown voltage	$V_{(\text{BR})\text{DSS}}$	$V_{\text{GS}} = 0\text{V}, I_D = 250\mu\text{A}$	20			V
Zero gate voltage drain current	I_{DSS}	$V_{\text{DS}} = 20\text{V}, V_{\text{GS}} = 0\text{V}$			1	μA
Gate-body leakage current	I_{GSS}	$V_{\text{GS}} = \pm 10\text{V}, V_{\text{DS}} = 0\text{V}$			± 20	μA
Gate threshold voltage ⁽²⁾	$V_{\text{GS}(\text{th})}$	$V_{\text{DS}} = V_{\text{GS}}, I_D = 250\mu\text{A}$	0.35	0.75	1.1	V
Drain-source on-resistance ⁽²⁾	$R_{\text{DS}(\text{on})}$	$V_{\text{GS}} = 4.5\text{V}, I_D = 650\text{mA}$		190	260	$\text{m}\Omega$
		$V_{\text{GS}} = 2.5\text{V}, I_D = 550\text{mA}$		260	360	
		$V_{\text{GS}} = 1.8\text{V}, I_D = 450\text{mA}$		390	590	
Forward transconductance	g_{FS}	$V_{\text{DS}} = 10\text{V}, I_D = 800\text{mA}$		1.6		S
Dynamic characteristics⁽⁴⁾						
Input Capacitance	C_{iss}	$V_{\text{DS}} = 16\text{V}, V_{\text{GS}} = 0\text{V}, f = 1\text{MHz}$		79	120	pF
Output Capacitance	C_{oss}			13	20	
Reverse Transfer Capacitance	C_{rss}			9	15	
Switching Characteristics⁽⁴⁾						
Turn-on delay time ⁽³⁾	$t_{\text{d}(\text{on})}$	$V_{\text{DS}} = 10\text{V}, I_D = 500\text{mA}, V_{\text{GS}} = 4.5\text{V}, R_G = 10\Omega$		6.7		ns
Turn-on rise time ⁽³⁾	t_r			4.8		ns
Turn-off delay time ⁽³⁾	$t_{\text{d}(\text{off})}$			17.3		ns
Turn-off fall time ⁽³⁾	t_f			7.4		ns
Source-Drain Diode characteristics						
Diode Forward voltage ⁽³⁾	V_{DS}	$I_S = 0.15\text{A}, V_{\text{GS}} = 0\text{V}$			1.2	V

Notes:

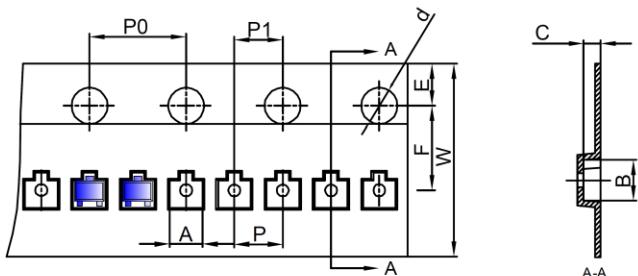
1. Surface mounted on FR4 board using the minimum recommended pad size.
2. Pulse Test : Pulse Width=300 μs , Duty Cycle=2%.
3. Switching characteristics are independent of operating junction temperatures.
4. Guaranteed by design, not subject to producting.

Typical Electrical and Thermal Characteristics

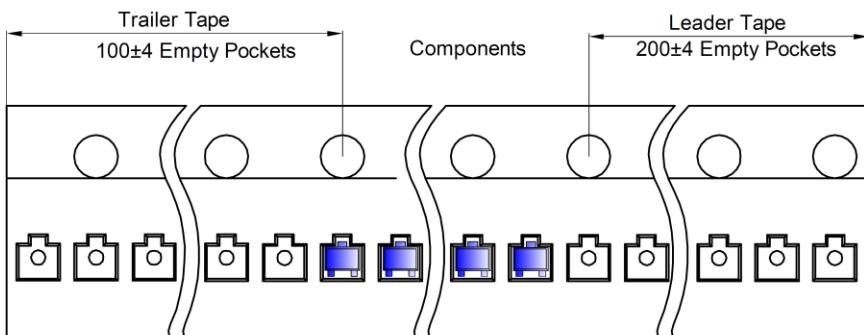
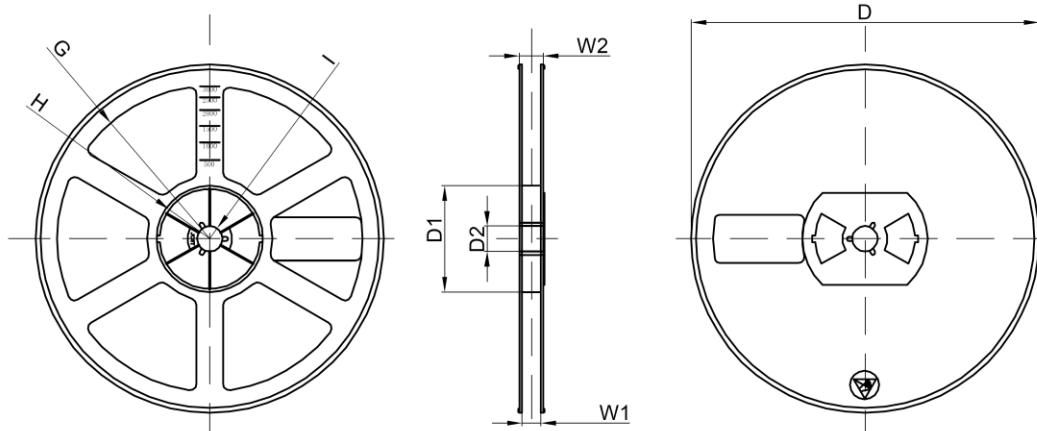


SOT-723 Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.320	0.400	0.013	0.016
A1	0.000	0.050	0.000	0.002
b	0.175	0.250	0.007	0.010
b1	0.225	0.300	0.009	0.012
c	0.090	0.130	0.004	0.005
D	1.170	1.230	0.046	0.048
E	1.150	1.250	0.045	0.049
E1	0.770	0.830	0.030	0.033
e	0.800TYP.		0.031TYP.	
theta	7° REF.		7° REF.	

SOT-723 Tape and Reel
SOT-723 Tape and reel
SOT-723 Embossed Carrier Tape


Dimensions are in millimeter										
Pkg type	A	B	C	d	E	F	P0	P	P1	W
SOT-723	1.33	1.45	0.61	Ø1.50	1.75	3.50	4.00	4.00	2.00	8.00

SOT-723 Tape Leader and Trailer

SOT-723 Reel


Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
7" Dia	Ø178.00	54.40	13.00	R78.00	R25.60	R6.50	9.50	12.30

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
8000 pcs	7 inch	80,000 pcs	203×203×195	320,000 pcs	438×438×220	